

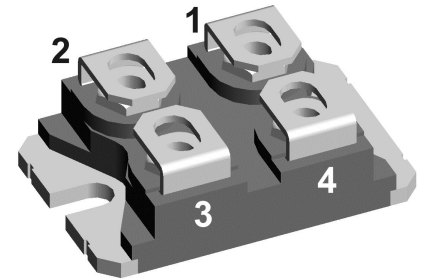
# HiPerFRED

$$\begin{aligned} V_{RRM} &= 1200 \text{ V} \\ I_{FAV} &= 2 \times 30 \text{ A} \\ t_{rr} &= 40 \text{ ns} \end{aligned}$$

High Performance Fast Recovery Diode  
Low Loss and Soft Recovery  
Parallel legs

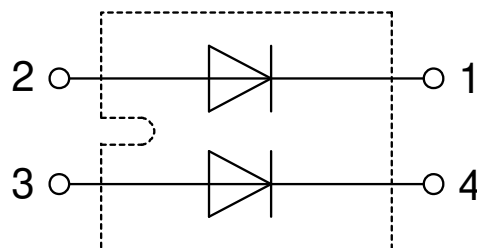
Part number

**DSEP2x31-12A**



Backside: isolated

 E72873



## Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low  $I_{rm}$ -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low  $I_{rm}$  reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

## Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

## Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling

## Terms and Conditions of Usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

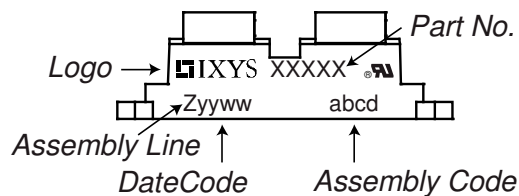
Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

- to perform joint risk and quality assessments;
- the conclusion of quality agreements;
- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V <sub>RSM</sub>	max. non-repetitive reverse blocking voltage	T <sub>VJ</sub> = 25°C				1200	V
V <sub>RRM</sub>	max. repetitive reverse blocking voltage	T <sub>VJ</sub> = 25°C				1200	V
I <sub>R</sub>	reverse current, drain current	V <sub>R</sub> = 1200 V	T <sub>VJ</sub> = 25°C			250	μA
		V <sub>R</sub> = 1200 V	T <sub>VJ</sub> = 150°C			1	mA
V <sub>F</sub>	forward voltage drop	I <sub>F</sub> = 30 A	T <sub>VJ</sub> = 25°C			2.72	V
		I <sub>F</sub> = 60 A				3.24	V
		I <sub>F</sub> = 30 A	T <sub>VJ</sub> = 150°C			1.77	V
		I <sub>F</sub> = 60 A				2.26	V
I <sub>FAV</sub>	average forward current	T <sub>C</sub> = 75°C rectangular      d = 0.5	T <sub>VJ</sub> = 150°C			30	A
V <sub>F0</sub>	threshold voltage	} for power loss calculation only				1.31	V
r <sub>F</sub>	slope resistance					15.4	mΩ
R <sub>thJC</sub>	thermal resistance junction to case					1.15	K/W
R <sub>thCH</sub>	thermal resistance case to heatsink				0.10		K/W
P <sub>tot</sub>	total power dissipation	T <sub>C</sub> = 25°C				100	W
I <sub>FSM</sub>	max. forward surge current	t = 10 ms; (50 Hz), sine; V <sub>R</sub> = 0 V				200	A
C <sub>J</sub>	junction capacitance	V <sub>R</sub> = 600 V   f = 1 MHz		T <sub>VJ</sub> = 25°C		12	pF
I <sub>RM</sub>	max. reverse recovery current	I <sub>F</sub> = 30 A; V <sub>R</sub> = 600 V		T <sub>VJ</sub> = 25 °C	8.5		A
				T <sub>VJ</sub> = 100 °C	13		A
t <sub>rr</sub>	reverse recovery time	-di <sub>F</sub> /dt = 200 A/μs		T <sub>VJ</sub> = 25 °C	60		ns
				T <sub>VJ</sub> = 100 °C	170		ns

Package SOT-227B (minibloc)				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I <sub>RMS</sub>	RMS current	per terminal				100	A
T <sub>VJ</sub>	virtual junction temperature			-40		150	°C
T <sub>op</sub>	operation temperature			-40		125	°C
T <sub>stg</sub>	storage temperature			-40		150	°C
Weight					30		g
M <sub>D</sub>	mounting torque			1.1		1.5	Nm
M <sub>T</sub>	terminal torque			1.1		1.5	Nm
d <sub>Spp/App</sub>	creepage distance on surface   striking distance through air	terminal to terminal	10.5	3.2			mm
d <sub>Spb/Apb</sub>		terminal to backside	8.6	6.8			mm
V <sub>ISOL</sub>	isolation voltage	t = 1 second	50/60 Hz, RMS; I <sub>ISOL</sub> ≤ 1 mA	3000			V
		t = 1 minute		2500			V

### Product Marking



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEP2x31-12A	DSEP2x31-12A	Tube	10	473286

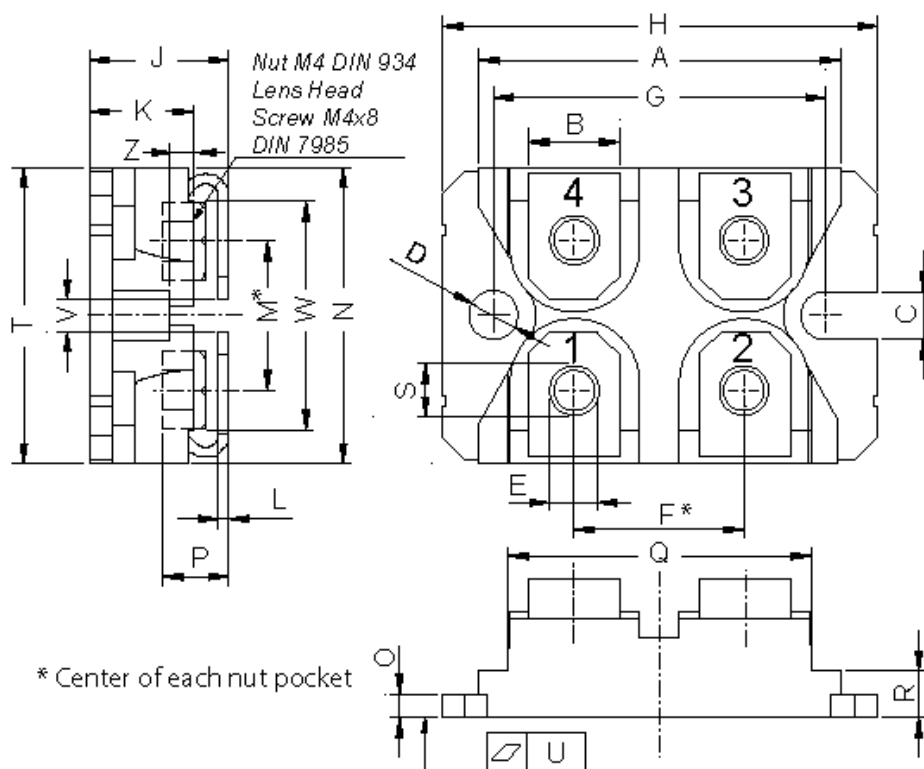
### Equivalent Circuits for Simulation

\* on die level

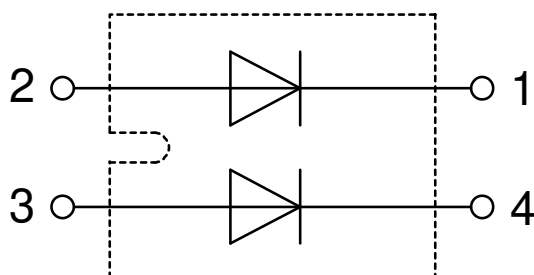
$T_{VJ} = 150^\circ\text{C}$

		<b>Fast Diode</b>	
$V_{0\max}$	threshold voltage	1.31	V
$R_{0\max}$	slope resistance *	13.5	mΩ

## Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106



## Fast Diode

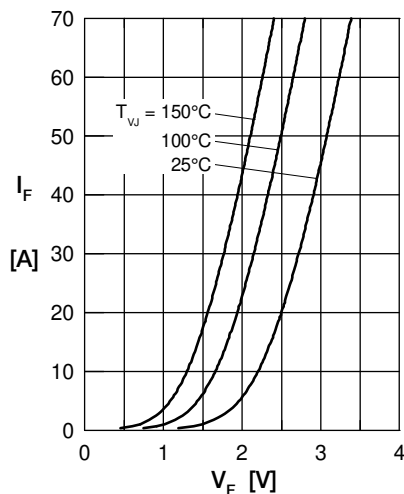


Fig. 1 Forward current  $I_F$  versus  $V_F$

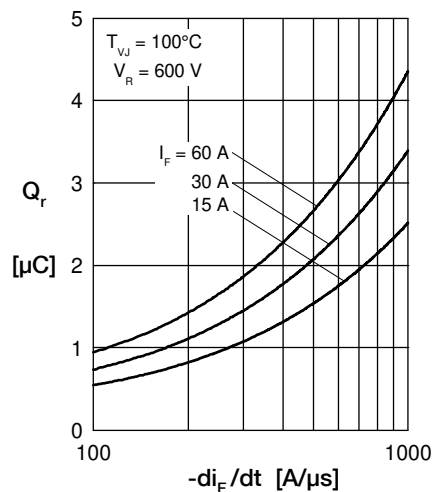


Fig. 2 Typ. reverse recov. charge  $Q_r$  versus  $-di_F/dt$

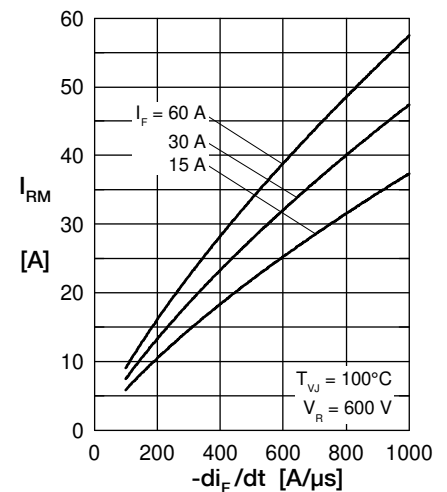


Fig. 3 Typ. peak reverse current  $I_{RM}$  versus  $-di_F/dt$

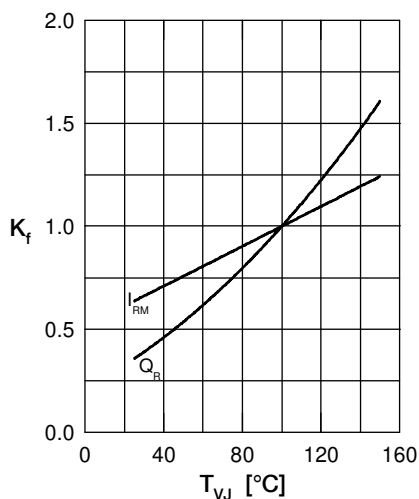


Fig. 4 Typ. dynamic parameters  $Q_r$ ,  $I_{RM}$  versus  $T_{VJ}$

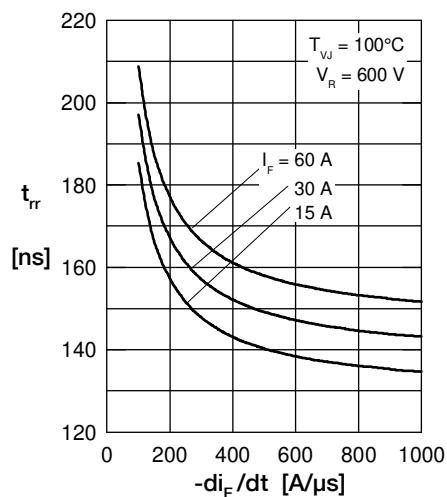


Fig. 5 Typ. recovery time  $t_{rr}$  versus  $-di_F/dt$

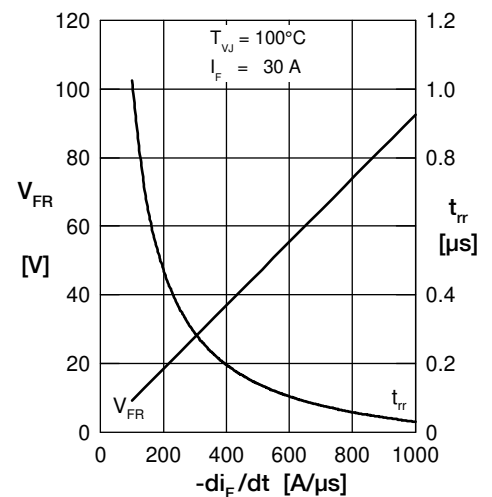


Fig. 6 Typ. peak forward voltage  $V_{FR}$  and  $t_{rr}$  versus  $di_F/dt$

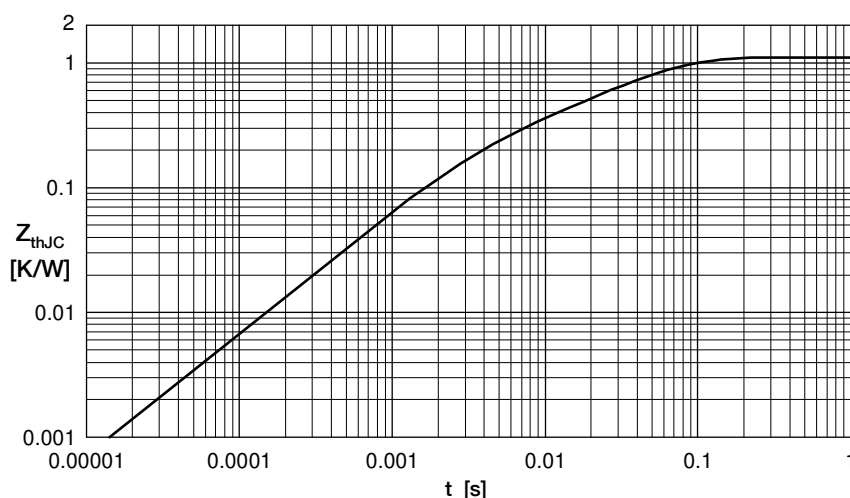


Fig. 7 Transient thermal impedance junction to case

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.368	0.0052
2	0.1417	0.0003
3	0.0295	0.0004
4	0.5604	0.0092